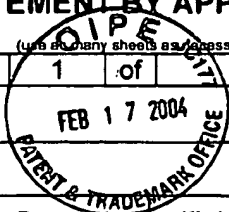


Substitute for form 1449A/PTO & 1449B/PTO		<b>Complete if Known</b>	
<b>FIRST INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)		Application Number	10/622,484
		Filing Date	July 21, 2003
		First Named Inventor	Michael SETTON
		Examiner Name	Unassigned <i>Pompey</i>
		Attorney Docket Number	015290-755
Sheet	1 of 2		



U.S. PATENT DOCUMENTS				
Examiner Initials	Document Number	Kind Code (if known)	Name of Patentee or Applicant of Cited Document	Issue/Publication Date (MM-DD-YYYY)
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<i>RP</i>	4,670,355		Matsudaira	06-1987
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					Yes	No
DP RP	0844647	A3	EPO	05-1998		
	60-107838		JAPAN	06-13-1985		

NON-PATENT LITERATURE DOCUMENTS	
Examiner Initials	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
<i>RP</i>	Alers, G.B. et al., "Nitrogen plasma annealing for low temperature Ta <sub>2</sub> O <sub>5</sub> films", Applied Physics Letters, vol. 72, no. 11, 1308-1310, 16 March 1998
<i>RP</i>	Campbell, S.A., et al., "MOSFET Transistors Fabricated with High Permittivity TiO <sub>2</sub> Dielectrics, IEEE Transactions on Electron Device, Vol. 44, No. 1, 104-109, January 1997.
<i>RP</i>	Cava, R.F. et al., "Enhancement of the dielectric constant of Ta <sub>2</sub> O <sub>5</sub> through substitution with TiO <sub>2</sub> ", Nature, Vol. 377, 215-217, 21 September 1995
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<i>RP</i>	Gan, J.-Y et al., "Dielectric property of (TiO <sub>2</sub> ) <sub>x</sub> -(Ta <sub>2</sub> O <sub>5</sub> ) <sub>1-x</sub> thin films", Appl. Phys. Lett. 72 (3), 19 January 1998, 332-334
<i>RP</i>	Hu, J.C. et al., "Feasibility of Using W/TiN as Metal Gate for conventional 0.13μm CMOS Technology and Beyond", IEEE, 1997

Examiner Signature	<i>Ron Pompey</i>	Date Considered	<i>12/17/04</i>
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with M.P.E.P. § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

Substitute for form 1449A/PTO & 1449B/PTO		<b>Complete if Known</b>	
<b>FIRST INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <small>(use if more than one disclosure is necessary)</small>		Application Number	10/622,484
		Filing Date	July 21, 2003
		First Named Inventor	Michael SETTON
		Examiner Name	Unassigned <i>Pompey</i>
Sheet	2 of 2	Attorney Docket Number	015290-755

FEB 17 2004 PATENT & TRADEMARK OFFICE		NON-PATENT LITERATURE DOCUMENTS
Examiner Initials	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
RP	Joshi, P.G., et al., "Structural and electrical properties of crystalline (1 - x) Ta <sub>2</sub> O <sub>5</sub> - xAl <sub>2</sub> O <sub>3</sub> thin films fabricated by metalorganic solution deposition technique", Apply. Phys. Lett. 71 (10), 8 September 1997, 1341-1343	
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RP	Chinese Official Action dated April 18, 2003 for Application No. 99808151.5	

Examiner Signature	Date Considered
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